Product data sheet

1. Product profile

1.1 General description

Planar Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a small hermetically sealed glass SOD80C Surface-Mounted Device SMD package with tin-plated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

1.2 Features

- Low forward voltage
- High breakdown voltage
- Guard-ring protected
- Hermetically sealed glass SMD package

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		-	-	200	mA
V_R	reverse voltage		-	-	30	V
V _F	forward voltage	$I_F = 100 \text{ mA}$	-	-	800	mV



Schottky barrier diode

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	
2	anode	k a	1 🖊 2
			sym001

^[1] The marking band indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	ber Package					
	Name	Description	Version			
BAS85	-	hermetically sealed glass surface-mounted package; 2 connectors	SOD80C			

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
BAS85	marking band

^[1] grey: made in Philippines purple: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage		-	30	V
I _F	forward current		-	200	mA
$I_{F(AV)}$	average forward current		<u>[1]</u> _	200	mA
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ s; } \delta \leq 0.5$	-	300	mA
I _{FSM}	non-repetitive peak forward current	$t_p = 10 \text{ ms}$	-	5	Α
Tj	junction temperature		-	125	°C
T_{amb}	ambient temperature		-65	+125	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	320	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

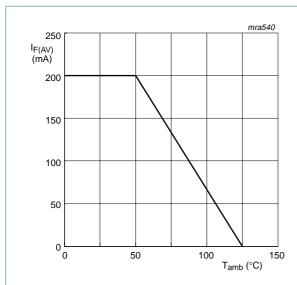
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forwa	forward voltage	$I_F = 0.1 \text{ mA}$	-	-	240	mV
		I _F = 1 mA	-	-	320	mV
		I _F = 10 mA	-	-	400	mV
		$I_F = 30 \text{ mA}$	-	-	500	mV
		I _F = 100 mA	-	-	800	mV
I_R	reverse current	V _R = 25 V	<u>[1]</u> -	-	2.3	μΑ
C_d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	-	10	pF

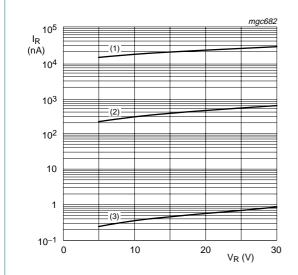
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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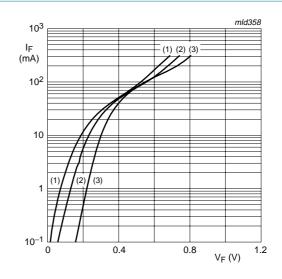
FR4 PCB, standard footprint

Fig 1. Average forward current as a function of ambient temperature; derating curve



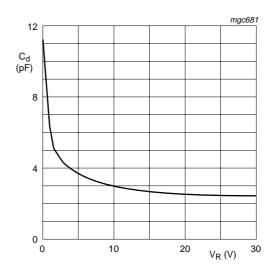
- (1) $T_{amb} = 85 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 3. Reverse current as a function of reverse voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 2. Forward current as a function of forward voltage; typical values



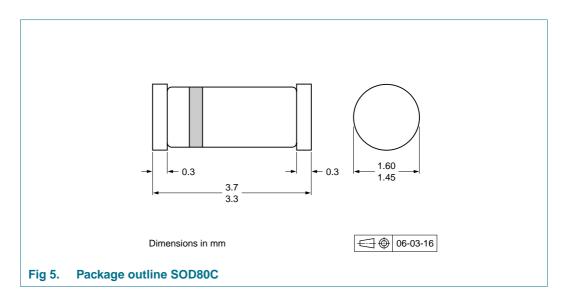
 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

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8. Package outline



9. Packing information

Table 8. Packing methods

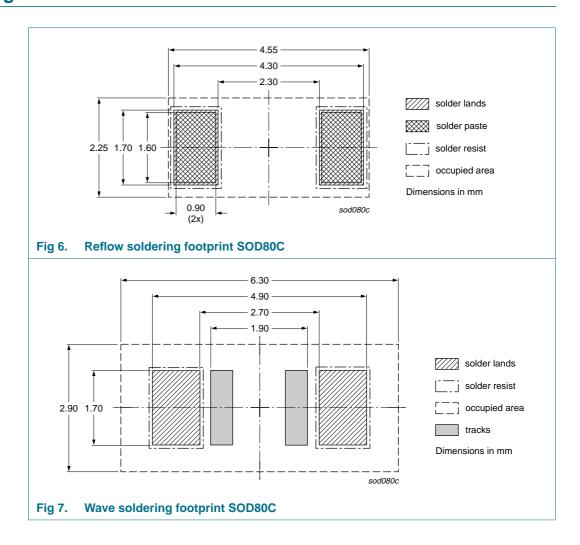
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			2500	10000
BAS85	SOD80C	4 mm pitch, 8 mm tape and reel	-115	-135

^[1] For further information and the availability of packing methods, see Section 13.

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10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BAS85_5	20090325	Product data sheet	-	BAS85_4		
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity		
	 Legal texts have been adapted to the new company name where appropriate. 					
	• Table 1 "Qu	ick reference data": added				
	Section 4 "Marking": enhanced					
	Figure 5: superseded by minimized package outline drawing					
	Section 9 "Packing information": added					
	Section 10 "Soldering": added					
	Section 12	"Legal information": updated	I			
BAS85_4	20000525	Product specification	-	BAS85_3		
BAS85_3	19961001	Product specification	-	BAS85_2		
BAS85_2	19960320	Product specification	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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